



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#31/E  
And  
J. McMillan

In re the Application of: SASHIDA, et al.

Group Art Unit: 2813 3/11/03

Serial No.: 09/321,605

Examiner: J. CHEN

Filed: May 28, 1999

P.T.O. Confirmation No.: 6725

For: **METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents  
Washington, D.C. 20231

February 27, 2003

Sir:

In response to the Office Action dated August 27, 2002, extended to February 27, 2003 by a three-month Petition for Extension of Time, please amend the above-identified application as follows

IN THE CLAIMS:

AMEND claims 1, 9, 14, 16 and 21 to read as follows:

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SUB  
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1. (Four Times Amended) A method of manufacturing a semiconductor device comprising the steps of:
- forming a couple of impurity diffusion layers in a semiconductor substrate;
  - forming a first insulating film covering the semiconductor substrate;
  - forming a lower electrode of a capacitor on the first insulating film;
  - forming an oxide dielectric film of the capacitor on the lower electrode;